

L Number	Hits	Search Text	DB	Time stamp
2	0	((source and drain) adj electrode) near10 pattern\$6 near10 (active adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/13 16:51
3	0	((source and drain) adj electrode) near10 expos\$6 near10 (active adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/13 16:53
4	20	((source and drain) adj electrode) near10 (active adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/13 16:53
-	18	chae-gee-sung.IN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/13 10:23
-	1040	"349" and (storage adj capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/13 10:24
-	30	"349" and (aperture adj ration)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/13 10:24
-	1365	"349" and (aperture adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/13 10:25
-	371	("349" and (storage adj capacitor)) and ("349" and (aperture adj ratio))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/13 10:26
-	191	(gate adj insulating adj film) near10 (overlap or cover) adj (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/13 10:29
-	318	(gate adj insulating adj film) near10 ((overlap or cover) adj (gate adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/13 10:30
-	107	(active adj layer) near10 (overlap or cover) near10 (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/13 10:31
-	0	(ohmic adj contact adj layer) adj on adj (active adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/13 10:32
-	322	(ohmic adj contact adj layer) near10 (active adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/13 10:33
-	377	(source adj electrode) near10 (ohmic adj contact adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/13 10:36

-	51	(drain adj electrode) near10 (ohmic adj contact adj layer) near10 (source adj electrode) near10 channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:38
-	3	(protective adj layer) near10 ((source and drain) adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:39
-	10	(storage adj electrode) near10 pixel near10 (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:23
-	2	(gate adj insulating adj film) near10 between near10 (pixel adj electrode) near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:54
-	0	((gate adj insulating adj film) near10 ((overlap or cover) adj (gate adj electrode))) and ((active adj layer) near10 (overlap or cover) near10 (gate adj electrode)) and ((ohmic adj contact adj layer) near10 (active adj layer)) and ((source adj electrode) near10 (ohmic adj contact adj layer)) and ((drain adj electrode) near10 (ohmic adj contact adj layer) near10 (source adj electrode) near10 channel) and ((protective adj layer) near10 ((source and drain) adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:55
-	6	((gate adj insulating adj film) near10 ((overlap or cover) adj (gate adj electrode))) and ((active adj layer) near10 (overlap or cover) near10 (gate adj electrode)) and ((ohmic adj contact adj layer) near10 (active adj layer)) and ((source adj electrode) near10 (ohmic adj contact adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:55
-	128	(storage adj electrode) near10 layer near10 (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:28
-	0	storage adj electrode adj layer adj gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:28
-	0	(pixel adj electrode) near10 (gate adj insulating adj film) near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:30
-	6	(pixel adj electrode) near10 (gate adj insulating adj film) near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:41
-	2	3789832.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:49
-	4	3731986.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:44

-	2	3057356.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:45
-	1	3641591.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:46
-	1	3541541.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:46
-	5	(contact adj hole) near10 connect near10 (source adj electrode) near10 (data adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 13:21
-	1	(contact adj hole) near10 connect near10 (source adj electrode) near10 (data adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 13:18
-	2	20020012078.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 13:19
-	9	(source adj electrode) near10 connect near10 (data adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 13:37
-	7	(metal adj layer) near10 (source and drain) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 13:29
-	3	"6335211"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 13:44
-	63	(contact adj hole) near10 connect\$6 near10 ((source and drain) adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 13:49
-	80	(contact adj hole) near10 connect\$6 near10 (source and data)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 13:58
-	16	(contact adj hole) near10 connect\$6 near10 ((source adj electrode) and (data adj line))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:03
-	0	(buffer adj layer) near10 cover\$6 near10 (source and drain) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:06
-	0	(buffer adj layer) near10 (source and drain) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:07

-	0	(buffer adj layer) near10 on near10 (source and drain) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:08
-	0	(buffer) near10 on near10 (source and drain) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:08
-	0	(metal) near10 on near10 (source and drain) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:09
-	1	(auxiliary adj storage adj electrode) near10 connect\$6 near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:12
-	4	(auxiliary adj storage adj electrode) near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:13
-	2	(auxiliary adj electrode) near10 connect\$6 near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:15
-	12969	(data adj line) near10 connect\$6 (source adj electrode) near10 (protective adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:20
-	1	(data adj line) near10 connect\$6 near10 (source adj electrode) near10 (protective adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:30
-	4	(data adj line) near10 (source adj electrode) near10 (protective adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:35
-	1	(data adj line) near10 connect\$6 near10 (source adj electrode) near10 (pierc\$6 or penetrat\$6) near10 (protective adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:39
-	13	buffer near10 (reduce adj contact adj resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:43
-	32	(protective adj layer) near10 (organic adj insulating adj material)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:46
-	2	(organic adj insulating adj material) near10 polytetrafluoroethylene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:55
-	76	(organic adj insulating adj material) near10 benzocyclobutene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:08

-	0	(organic adj insulating adj material) near10 (perfluoropolymer adj resin)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:56
-	1	(organic adj insulating adj material) near10 (perfluoropolymer adj resin)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:56
-	1	(organic adj insulating adj material) near10 (perfluoropolymer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:57
-	0	(organic adj insulator) near10 (perfluoropolymer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:57
-	0	perfluoropolymer adj resin near10 (insulating or insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:58
-	0	(perfluoropolymer adj resin) near10 (insulating or insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:58
-	0	perfluoropolymer adj resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:59
-	7	perfluoropolymer adj resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 14:59
-	42	(passivation adj layer) near10 (organic adj insulating adj material)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:15
-	0	((data and gate) adj perpendicular) near10 connect\$6 near10 (source adj electrode) near10 (passivation adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:19
-	9	(data adj line) near10 connect\$6 near (source adj electrode) near10 (passivation adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:23
-	42	(passivation adj layer) near10 (organic adj insulating adj material)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:27
-	0	(data adj line) near10 connect\$6 near10 (source adj electrode) near10 ((pierc\$6 or penetrat\$6) adj passivation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:30
-	0	(data adj line) near10 (source adj electrode) near10 ((pierc\$6 or penetrat\$6) adj passivation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:31

-	1	(data adj line) near10 ((pierc\$6 or penetrat\$6) adj passivation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:31
-	2	(data adj line) near10 ((pierc\$6 or penetrat\$6) near10 passivation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:33
-	0	(data adj line) near10 (source adj electrode) near10 ((pierc\$6 or penetrat\$6) near10 passivation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:35
-	0	(data adj line) near10 connect\$6 near10 (source adj electrode) near10 ((pierc\$6 or penetrat\$6) near10 passivation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:37
-	530	(data adj line) near10 connect\$6 near10 (source adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:40
-	210	(data adj line) near10 ((passivation or protective) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:42
-	84	((data adj line) near10 connect\$6 near10 (source adj electrode)) and ((data adj line) near10 ((passivation or protective) adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:47
-	56	(data adj line) near10 (source adj electrode) near10 (passivation adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:53
-	2	(data adj line) near10 (pierc\$6 or penetrat\$6) near10 (passivation adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 16:03
-	610	(contact adj hole) near10 ((protective or passivation) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:59
-	129	((data adj line) near10 connect\$6 near10 (source adj electrode)) and ((contact adj hole) near10 ((protective or passivation) adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 15:59
-	12	(data adj line) near10 (source adj electrode) near10 (contact adj hole) near10 (passivation adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 16:09
-	4	(data adj line) near10 connect\$6 near10 (source adj electrode) near10 (contact adj hole) near10 (passivation adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 16:29
-	0	(SOURCE AND DRAIN) NEAR10 PATTERNING NEAR10 (ACTIVE ADJ LAYER)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 16:30

-	0	(source and drain) near10 patterning near10 (active adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 16:31
-	5	patterning near10 (active adj layer) near10 (source and drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 16:32

L Number	Hits	Search Text	DB	Time stamp
5	18	chae-gee-sung.IN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:23
6	1040	"349" and (storage adj capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:24
7	30	"349" and (aperture adj ration)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:24
8	1365	"349" and (aperture adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:25
9	371	("349" and (storage adj capacitor)) and ("349" and (aperture adj ratio))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:26
10	191	(gate adj insulating adj film) near10 (overlap or cover) adj (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:29
11	318	(gate adj insulating adj film) near10 ((overlap or cover) adj (gate adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:30
12	107	(active adj layer) near10 (overlap or cover) near10 (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:31
13	0	(ohmic adj contact adj layer) adj on adj (active adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:32
14	322	(ohmic adj contact adj layer) near10 (active adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:33
15	377	(source adj electrode) near10 (ohmic adj contact adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:36
16	51	(drain adj electrode) near10 (ohmic adj contact adj layer) near10 (source adj electrode) near10 channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:38
17	3	(protective adj layer) near10 ((source and drain) adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:39
18	10	(storage adj electrode) near10 pixel near10 (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:23

19	2	(gate adj insulating adj film) near10 between near10 (pixel adj electrode) near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:54
20	0	((gate adj insulating adj film) near10 ((overlap or cover) adj (gate adj electrode))) and ((active adj layer) near10 (overlap or cover) near10 (gate adj electrode)) and ((ohmic adj contact adj layer) near10 (active adj layer)) and ((source adj electrode) near10 (ohmic adj contact adj layer)) and ((drain adj electrode) near10 (ohmic adj contact adj layer) near10 (source adj electrode) near10 channel) and ((protective adj layer) near10 ((source and drain) adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:55
21	6	((gate adj insulating adj film) near10 ((overlap or cover) adj (gate adj electrode))) and ((active adj layer) near10 (overlap or cover) near10 (gate adj electrode)) and ((ohmic adj contact adj layer) near10 (active adj layer)) and ((source adj electrode) near10 (ohmic adj contact adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 10:55
22	128	(storage adj electrode) near10 layer near10 (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:28
23	0	storage adj electrode adj layer adj gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:28
24	0	(pixel adj electrode) near10 (gate adj insulating adj film) near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:30
25	6	(pixel adj electrode) near10 (gate adj insulating adj film) near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:41
26	2	3789832.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:43
27	4	3731986.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:44
28	2	3057356.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:45
30	1	3641591.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:46
31	1	3541541.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/13 11:46